

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TPV7025** is Designed for Television Band IV & V Applications up to 860 MHz.

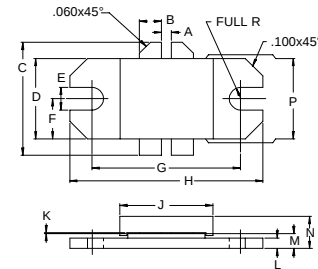
FEATURES:

- Common Emitter
- $P_G = 9.0$ dB at 25 W/860 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	8.0 A
V_{CBO}	45 V
V_{CEO}	28 V
V_{EBO}	4.0 V
P_{DISS}	86 W @ $T_C = 70^\circ\text{C}$
T_J	-50°C to $+200^\circ\text{C}$
T_{STG}	-50°C to $+200^\circ\text{C}$
θ_{JC}	1.5°C/W

PACKAGE STYLE .450 BAL FLG(A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.055 / 1.40	
B	.120 / 3.05	.130 / 3.30
C	.785 / 19.94	
D	.455 / 11.56	.465 / 11.81
E	.120 / 3.05	.130 / 3.30
F	.230 / 5.84	
G	.838 / 21.28	.850 / 21.59
H	1.095 / 27.81	1.105 / 28.07
J	.525 / 13.34	.535 / 13.59
K	.002 / 0.05	.005 / 0.15
L	.055 / 1.40	.065 / 1.65
M	.080 / 2.03	.095 / 2.41
N	.195 / 4.95	
P	.445 / 11.30	.455 / 11.56

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 20$ mA			45			V
BV_{CEO}	$I_C = 120$ mA			28			V
BV_{EBO}	$I_E = 20$ mA			4.0			V
h_{FE}	$V_{CE} = 20$ V	$I_C = 1.0$ A		10		60	---
C_{OB}	$V_{CB} = 28$ V	$f = 1.0$ MHz		64		80	pF
P_G IMD_1	$V_{CE} = 25$ V $P_{OUT} = 25$ W	$I_C = 3.2$ A $f = 860$ MHz		9.0		10.5 -45	dB dBc